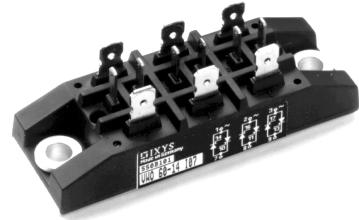
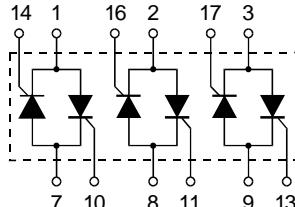


Three Phase AC Controller Modules

$I_{RMS} = 3 \times 39 A$
 $V_{RRM} = 800-1600 V$

Preliminary data

V_{RSM} V _{DSM} V	V_{RRM} V _{DRM} V	Type
800	800	VWO 36-08io7
1200	1200	VWO 36-12io7
1400	1400	VWO 36-14io7
1600	1600	VWO 36-16io7



Symbol	Test Conditions	Maximum Ratings		
I_{RMS}	$T_K = 85^\circ C$, 50 - 400 Hz (per phase)	39	A	
I_{TRMS}	$T_{VJ} = T_{VJM}$	28	A	
I_{TAVM}	$T_K = 85^\circ C$; (180° sine)	18	A	
I_{TSM}	$T_{VJ} = 45^\circ C$; $V_R = 0$	320	A	
	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	350	A	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	280	A	
	$t = 10 \text{ ms}$ (50 Hz), sine $t = 8.3 \text{ ms}$ (60 Hz), sine	310	A	
I^2t	$T_{VJ} = 45^\circ C$ $V_R = 0$	500	A^2s	
		520	A^2s	
	$T_{VJ} = T_{VJM}$ $V_R = 0$	390	A^2s	
		400	A^2s	
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu s$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$ $di_G/dt = 0.3 \text{ A}/\mu s$	150	$A/\mu s$	
	repetitive, $I_T = 20 \text{ A}$			
	non repetitive, $I_T = I_{TAVM}$	500	$A/\mu s$	
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	$V/\mu s$	
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	10	W	
		5	W	
P_{GAVM}		0.5	W	
V_{RGM}		10	V	
T_{VJ}		-40...+125	$^\circ C$	
T_{VJM}		125	$^\circ C$	
T_{stg}		-40...+125	$^\circ C$	
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500 3000	V~	
M_d	Mounting torque (M5) (10-32 UNF)	$5 \pm 15 \%$ $44 \pm 15 \%$	Nm lb.in.	
Weight	typ.	110	g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$; $V_D = V_{DRM}$	≤	5	mA
V_T	$I_T = 45 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	≤	1.45	V
V_{TO}	For power-loss calculations only	0.85	V	
r_T		13	mΩ	
V_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	≤	1.0	V
	$T_{VJ} = -40^\circ\text{C}$	≤	1.2	V
I_{GT}	$V_D = 6 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	≤	65	mA
	$T_{VJ} = -40^\circ\text{C}$	≤	80	mA
V_{GD}	$T_{VJ} = T_{VJM}$; $V_D = 2/3 V_{DRM}$	≤	0.2	V
I_{GD}		≤	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}$; $t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}$; $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	150	mA
I_H	$T_{VJ} = 25^\circ\text{C}$; $V_D = 6 \text{ V}$; $R_{GK} = \infty$	≤	100	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}$; $V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}$; $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	2	μs
t_q	$T_{VJ} = T_{VJM}$; $I_T = 20 \text{ A}$, $t_p = 200 \mu\text{s}$; $di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$; $dv/dt = 15 \text{ V}/\mu\text{s}$; $V_D = 2/3 V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor; sine 180°el	1.3	K/W	
	per module	0.216	K/W	
R_{thJK}	per thyristor; sine 180°el	1.5	K/W	
	per module	0.25	K/W	
d_s	Creeping distance on surface	16.1	mm	
d_A	Creepage distance in air	6.0	mm	
a	Max. allowable acceleration	50	m/s^2	

Dimensions in mm (1 mm = 0.0394")

